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July 15, 2026

MEMORANDUM FOR MILITARY/INDUSTRY DISTRIBUTION

SUBJECT: Initial Draft of Performance Specification Sheet MIL-PRF-19500/760B,
Project Number 5961-2026-072.

The initial draft for this subject document, dated July 15, 2026, is now available for viewing and downloading from the DLA Weapons Support-VA Web site:

<https://LandandMaritimeApps.dla.mil/Programs/MilSpec/DocSearch.aspx>

The initial draft of the subject document was generated to update the U2A case outline and to update it to the latest document format and various editorial changes to bring it into compliance with MIL-STD-961. Highlighting has been used for easy change recognition.

Concurrence or comments are required at this Center within 30 days from the date of this letter (August 14, 2026). Late comments will be held for the next coordination of the document. Comments from military departments must be identified as either "Essential" or "Suggested". Essential comments must be justified with supporting data. Military review activities should forward comments to their custodians of this office, as applicable, in sufficient time to allow for consolidating the department reply.

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/ Signed /

MUHAMMAD AKBAR
Chief
Active Devices Branch

NOTE: This draft, dated **15 Julu 2026** prepared by DLA – CC, has not been approved and is subject to modification. DO NOT USE PRIOR TO APPROVAL.
(Project 5961-2026-072)
COMMENTS ARE DUE BY 14 August 2026.
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INCH-POUND

MIL-PRF-19500/760B
DRAFT
SUPERSEDING
MIL-PRF-19500/760A
w/AMENDMENT 5
25 August 2025

PERFORMANCE SPECIFICATION SHEET

TRANSISTOR, FIELD EFFECT RADIATION HARDENED, N-CHANNEL, SILICON,
ENCAPSULATED (SURFACE MOUNT PACKAGE), TYPES 2N7579, 2N7581, 2N7583, AND 2N7585,
JANTXV, AND JANS

This specification is approved for use by all Departments
and Agencies of the Department of Defense.

The requirements for acquiring the product described herein shall consist of
this specification sheet and [MIL-PRF-19500](#).

1. SCOPE

1.1 Scope. This specification covers the performance requirements for a N-channel, enhancement-mode, MOSFET, radiation hardened (total dose and single event effects (SEE)), power transistor. Two levels of product assurance (JANTXV and JANS) are provided for each encapsulated device, with avalanche energy maximum rating (E_{AS}) and maximum avalanche current (I_{AS}). Provisions for radiation hardness assurance (RHA) to three radiation levels ("R", "F", and "G") are provided for JANTXV and JANS product assurance levels.

1.2 Package outlines. The device package outlines are as follows: TO-276AC in accordance with [figure 1](#) for all encapsulated device types and surface mount (U2A) in accordance with [figure 2](#) for all encapsulated device types.

* 1.3 Maximum ratings. T_A = +25°C, unless otherwise specified.

Type	P _T (2) T _C = +25°C	P _T T _A = +25°C	R _{θJC} (3)	V _{DS}	V _{DG}	V _{GS}	I _{D1} (4) (5) T _C = +25°C	I _{D2} T _C = +100°C	I _S	I _{DM} (6)	T _J and T _{STG}
	<u>W</u>	<u>W</u>	<u>°C/W</u>	<u>V dc</u>	<u>V dc</u>	<u>V dc</u>	<u>A dc</u>	<u>A dc</u>	<u>A dc</u>	<u>A (pk)</u>	<u>°C</u>
2N7579U2	250	1.56	0.5	100	100	±20	56	56	56	224	-55
2N7581U2	250	1.56	0.5	150	150	±20	56	49	56	224	to
2N7583U2	250	1.56	0.5	200	200	±20	56	40	56	224	+150
2N7585U2	250	1.56	0.5	250	250	±20	50	31.5	50	200	

- (1) Electrical characteristics for the "U2A" suffix devices are identical to the "U2" suffix devices unless otherwise noted.
- (2) Derate linearly by 2.0 W/°C for T_C > +25°C.
- (3) See [figure 3](#), thermal impedance curves.
- (4) The following formula derives the maximum theoretical I_D limit. I_D is limited to 56 A (by package and internal wires and may be limited by pin diameter):

$$I_D = \sqrt{\frac{T_{JM} - T_C}{(R_{\theta JC}) \times (R_{DS(on)} \text{ at } T_{JM})}}$$

- (5) See [figure 4](#), maximum drain current graph.
- (6) I_{DM} = 4 X I_{D1}; I_{D1} as calculated by footnote (4).

Comments, suggestions, or questions on this document should be addressed to DLA **Land and Maritime Weapons Support**, ATTN: VAC, P.O. Box 3990, Columbus, OH 43218-3990, or emailed to Semiconductor@dla.mil. Since contact information can change, you may want to verify the currency of this address information using the ASSIST Online database at <https://assist.dla.mil/>.

AMSC N/A

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FSC 5961



1.4 Primary electrical characteristics at $T_C = +25^\circ\text{C}$.

Type	Min $V_{(BR)DSS}$ $V_{GS} = 0$ $I_D = 1.0\text{mA dc}$	$V_{GS(TH)1}$ $V_{DS} \geq V_{GS}$ $I_D = 1.0\text{ mA dc}$	Max I_{DSS1} $V_{GS} = 0$ $V_{DS} = 80\%$ of rated V_{DS}	Max $r_{DS(on)}$ (2) $V_{GS} = 12\text{V}$, $I_D = I_{D2}$		V_{ISO} 70,000 ft. altitude	E_{AS}
				$T_J = +25^\circ\text{C}$	$T_J = +150^\circ\text{C}$		
	<u>V dc</u>	<u>V dc</u> <u>Min</u> <u>Max</u>	<u>$\mu\text{A dc}$</u>	<u>Ω</u>	<u>Ω</u>	<u>V dc</u>	<u>mJ</u>
2N7579U2	100	2.0 4.0	10	0.010	0.020		462
2N7581U2	150	2.0 4.0	10	0.018	0.0414		283
2N7583U2	200	2.0 4.0	10	0.028	0.063		268
2N7585U2	250	2.0 4.0	10	0.040	0.100	250	240

(1) Electrical characteristics for the "U2A" suffix devices are identical to the "U2" suffix devices unless otherwise noted.

(2) Pulsed (see 4.5.1).

1.5 Part or Identifying Number (PIN). The PIN is in accordance with MIL-PRF-19500, and as specified herein. See 6.4 for PIN construction example and 6.5 for a list of available PINs.

1.5.1 JAN certification mark and quality level for encapsulated devices. The quality level designators for encapsulated devices that are applicable for this specification sheet from the lowest to the highest level are as follows: "JANTXV" and "JANS".

1.5.2 Radiation hardness assurance (RHA) designator. The RHA levels that are applicable for this specification sheet from lowest to highest are as follows: "R", "F" and "G".

1.5.3 Device type. The designation system for the device types of transistors covered by this specification sheet are as follows.

1.5.3.1 First number and first letter symbols. The transistors of this specification sheet use the first number and letter symbols "2N".

1.5.3.2 Second number symbols. The second number symbols for the transistors covered by this specification sheet are as follows: "7579", "7581", "7583", and "7585".

1.5.3.3 Suffix letters. The suffix letters "U2" are used on devices that are packaged in the SMD2 TO-276AC package of figure 1. The suffix letters "U2A" are used on devices that are packaged in the surface mount package of figure 2.

1.5.4 Lead finish. The lead finishes applicable to this specification sheet are listed on QPDSIS-19500.

* 1.6 Radiation features. The following radiation features are applicable for RHA devices supplied to this specification sheet.

* 1.6.1 Maximum total ionizing dose (TID). The maximum TID that RHA devices were tested to in accordance with condition A (dose rate = 50 to 300 rad(Si)/s) of method 1019 of [MIL-STD-750](#) are as follows:

For device type 2N7585U2 AND 2N7585U2A: 100 krad(Si) 1/
For device type 2N7579U2, 2N7579U2A, 2N7581U2, AND 2N7581U2A: 300 krad(Si) 1/
For device type 2N7583U2 AND 2N7583U2A: 500 krad(Si) 1/

* 1.6.2 Heavy ion irradiation SEE. SEE testing includes Single-Event Burnout (SEB) and Single-Event Gate Rupture (SEGR) tests at the specified linear energy transfer (LET) units. See [6.7](#) for the specific RHA SEE characterization testing details. The following characterization conditions were used for the testing to the requirements herein:

For device type 2N7579:

No SEB or SEGR were observed at surface LET (see [table IV](#)) $\leq 90 \text{ MeV} \cdot \text{cm}^2/\text{mg}$ 2/
(In-situ Bias $V_{DS} = 100 \text{ V}$ and $V_{GS} = -5 \text{ V}$)

For device type 2N7581:

No SEB or SEGR were observed at surface LET (see [table IV](#)) $\leq 90 \text{ MeV} \cdot \text{cm}^2/\text{mg}$ 2/
(In-situ Bias $V_{DS} = 50 \text{ V}$ and $V_{GS} = -5 \text{ V}$)
(In-situ Bias $V_{DS} = 30 \text{ V}$ and $V_{GS} = -10 \text{ V}$)

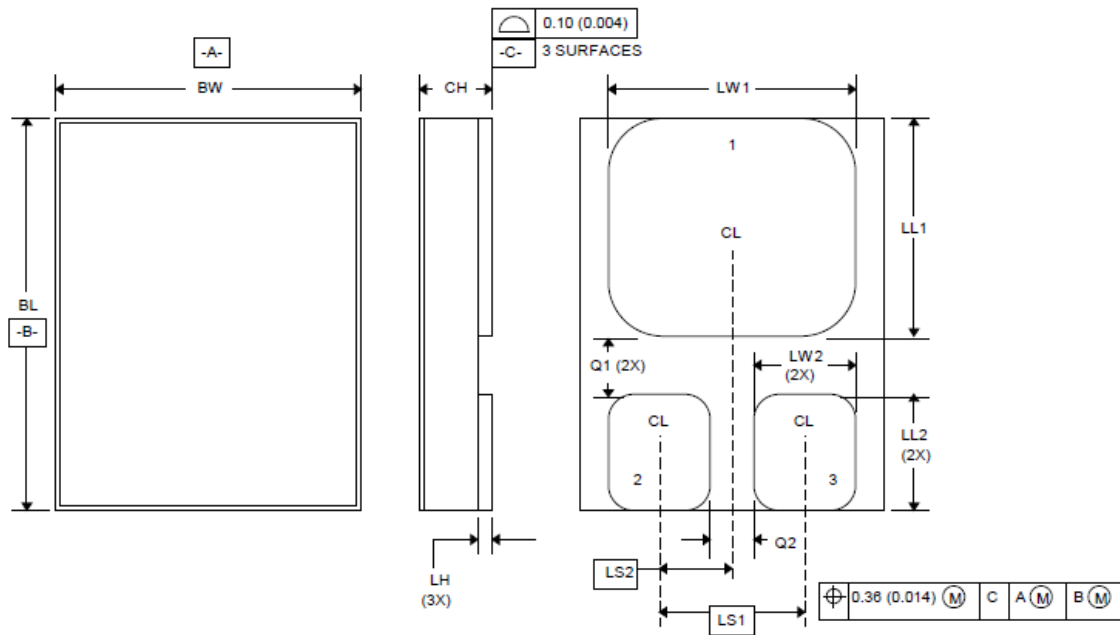
For device type 2N7583:

No SEB or SEGR were observed at surface LET (see [table IV](#)) $\leq 90 \text{ MeV} \cdot \text{cm}^2/\text{mg}$ 2/
(In-situ Bias $V_{DS} = 150 \text{ V}$ and $V_{GS} = -4 \text{ V}$)
(In-situ Bias $V_{DS} = 110 \text{ V}$ and $V_{GS} = -5 \text{ V}$)

For device type 2N7585:

No SEB or SEGR were observed at surface LET (see [table IV](#)) $\leq 90 \text{ MeV} \cdot \text{cm}^2/\text{mg}$ 2/
(In-situ Bias $V_{DS} = 75 \text{ V}$ and $V_{GS} = -5 \text{ V}$)

- * 1/ The manufacturers supplying these device types have performed characterization testing in accordance with condition A (dose rate = 50 to 300 rad(Si)/s) of method 1019 of [MIL-STD-750](#). The radiation end point limits are guaranteed only to a maximum TID level of 100, 300, or 500 krad(Si).
- * 2/ The manufacturers have performed SEE tests at Texas A&M University (TAMU) Radiation Effects Facility in accordance with method 1080 of [MIL-STD-750](#). For more information on SEE testing and results, customers should contact the qualified manufacturer.

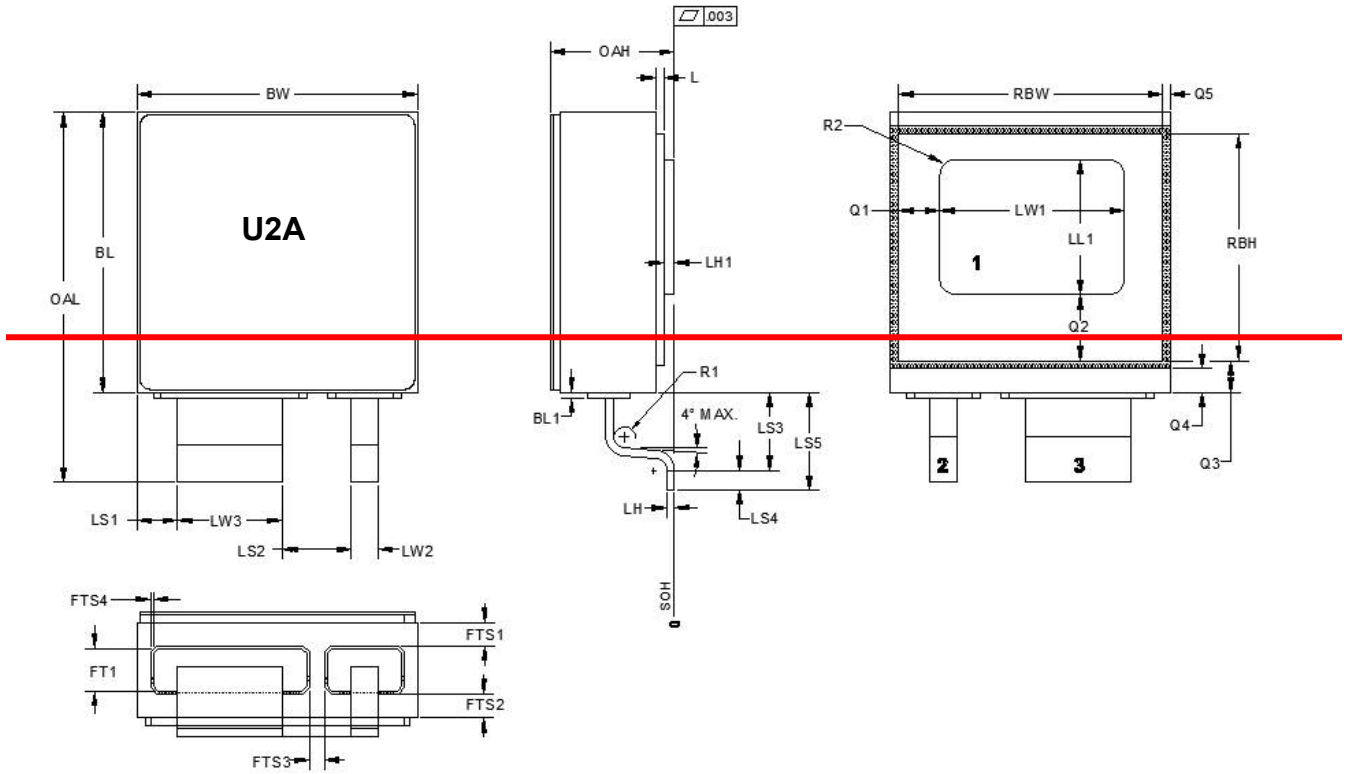


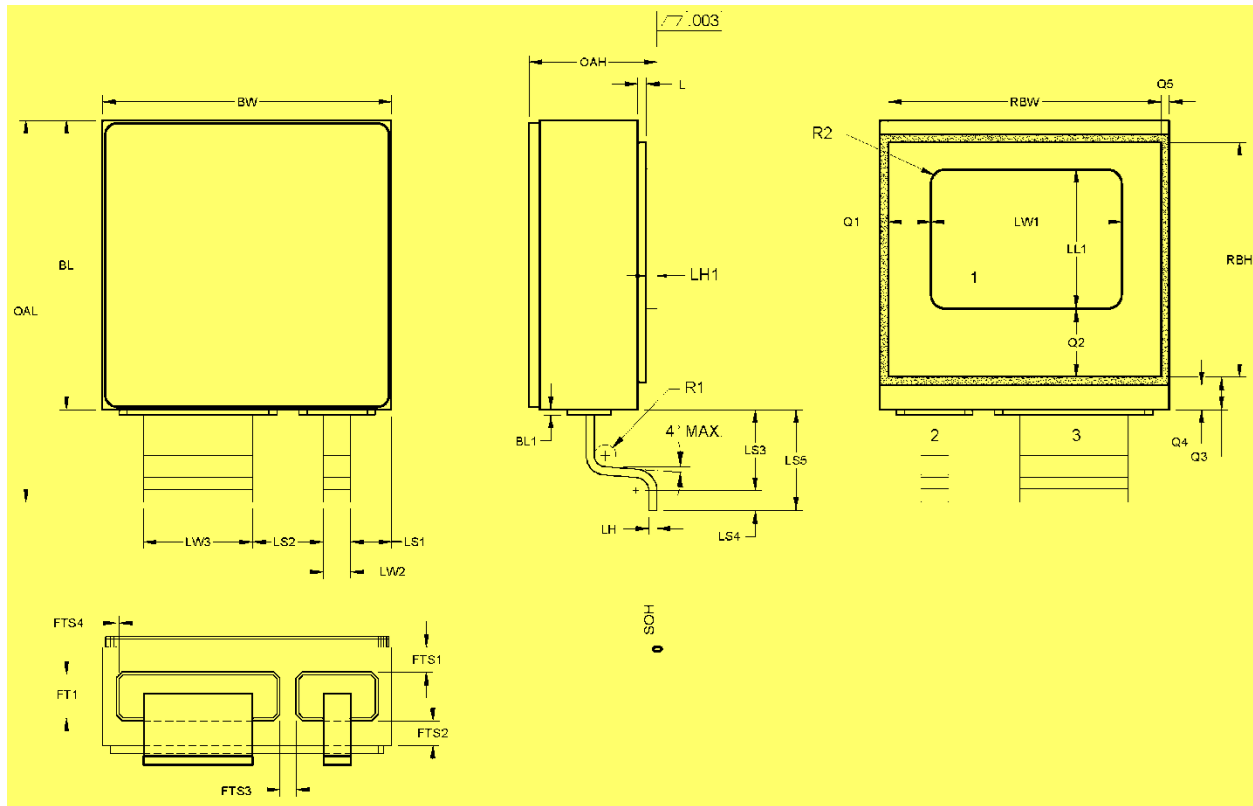
Symbol	Dimensions			
	Inches		Millimeters	
	Min	Max	Min	Max
BL	.685	.695	17.40	17.65
BW	.520	.530	13.21	13.46
CH		.142		3.60
LH	.010	.020	0.26	0.50
LW1	.435	.445	11.05	11.30
LW2	.135	.145	3.43	3.68
LL1	.470	.480	11.94	12.19
LL2	.152	.162	3.86	4.12
LS1	.240 BSC		6.10 BSC	
LS2	.120 BSC		3.05 BSC	
Q1	.035		0.89	
Q2	.050		1.27	
Term 1	Drain			
Term 2	Gate			
Term 3	Source			

* NOTES:

1. Dimensions are in inches.
2. Millimeters are given for general information only.
3. Terminal 1 - Drain, Terminal 2 - Gate, Terminal 3 - Source.

FIGURE 1. Physical dimensions for surface mount U2 (TO-276AC).





*

FIGURE 2. Physical dimensions, U2A surface mount.

Symbol	Dimensions			
	Inches		Millimeters	
	Min	Max	Min	Max
BL	.524	.536	13.31	13.61
BL1	.005	.015	0.13	0.38
BW	.524	.536	13.31	13.61
FT1	.075	.085	1.91	2.16
FTS1	.036		0.91	
FTS2	.036		0.91	
FTS3	.030		0.76	
FTS4	.005 TYP		0.127 TYP	
L	.013	.017	0.33	0.43
LH	.013	.017	0.33	0.43
LH1	.02	.024	0.51	0.61
LL1	.25	.26	6.35	6.60
LS1	.07	.08	1.78	2.03
LS2	.125	.135	3.18	3.43
LS3	~~.125~~ .130	~~.145~~ .140	~~3.18~~ 3.30	~~3.68~~ 3.56
LS4	.040	.050	1.02	1.27
LS5	.170	.190	4.32	4.83
LW1	.345	.355	8.76	9.02
LW2	.045	.055	1.14	1.4
LW3	.195	.205	4.95	5.21
OAH		.26		6.60
OAL	.71 TYP		18.03 TYP	
Q1	.073	.083	1.85	2.11
Q2	.12	.13	3.05	3.30
Q3	.055	.065	1.40	1.65
Q4	.04		1.02	
Q5	.010	.020	.25	.51
RBH	.425	.435	10.8	11.05
RBW	.495	.505	12.57	12.83
R1	.02		0.51	
R2	.025	.035	0.635	0.889
TERM 1	Drain			
TERM 2	Gate			
TERM 3	Source			

NOTES:

1. Dimensions are in inches.
2. Millimeters are given for general information only.

FIGURE 2. Physical dimensions, U2A surface mount – continued

* 2. APPLICABLE DOCUMENTS PUBLICATIONS

2.1 General. The documents listed in this section are specified in sections 3 and 4 of this specification. This section does not include documents cited in other sections of this specification or recommended for additional information or as examples. While every effort has been made to ensure the completeness of this list, document users are cautioned that they must meet all specified requirements of documents cited in sections 3 and 4 of this specification, whether or not they are listed.

2.2 Government documents.

2.2.1 Specifications, standards, and handbooks. The following specifications, standards, and handbooks form a part of this document to the extent specified herein. Unless otherwise specified, the issues of these documents are those cited in the solicitation or contract.

DEPARTMENT OF DEFENSE SPECIFICATIONS

MIL-PRF-19500 - Semiconductor Devices, General Specification for.

DEPARTMENT OF DEFENSE STANDARDS

MIL-STD-750 - Test Methods for Semiconductor Devices.
MIL-STD-883 - Test Method Standard Microcircuits

(Copies of these documents are available online at <https://quicksearch.dla.mil/>).

2.3 Order of precedence. Unless otherwise noted herein or in the contract, in the event of a conflict between the text of this document and the references cited herein, the text of this document takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

3. REQUIREMENTS

3.1 General. The individual item requirements shall be as specified in MIL-PRF-19500 and as modified herein.

3.2 Qualification. Devices furnished under this specification shall be products that are manufactured by a manufacturer authorized by the qualifying activity for listing on the applicable qualified manufacturer's list (QML) before contract award (see 4.2 and 6.3).

3.3 Abbreviations, symbols, and definitions. Abbreviations, symbols, and definitions used herein shall be as specified in MIL-PRF-19500.

* 3.4 Interface and physical dimensions. Interface and physical dimensions shall be as specified in MIL-PRF-19500, and on figure 1 (TO-276AC) and figure 2 (U2A) herein.

3.4.1 Lead finish. Lead finish shall be solderable in accordance with MIL-PRF-19500, MIL-STD-750, and herein. Where a choice of lead finish is desired, it shall be specified in the acquisition document (see 6.2).

3.4.2 Multiple chip construction. Multiple chip construction is not permitted to meet the requirements of this specification.

* 3.4.3 Silicone die coat. The use of a silicone die coat requires a successful completion of method 5011 of MIL-STD-883, on each lot of silicone die coating for its intended applications.

3.5 Electrostatic discharge sensitive (ESDS). The devices covered by this specification sheet have been classified as ESDS. The devices shall be handled in accordance with the ESD program established to comply with the requirements of [MIL-PRF-19500](#) to avoid damage due to the accumulation of static charge. The following handling practices shall be followed:

- a. Devices should be handled on benches with conductive handling devices.
- b. Ground test equipment, tools, and personnel handling devices.
- c. Do not handle devices by the leads.
- d. Store devices in conductive foam or carriers.
- e. Avoid use of plastic, rubber or silk in MOS areas.
- f. Maintain relative humidity above 50 percent if practical.
- g. Care should be exercised during test and troubleshooting to apply not more than maximum rated voltage to any lead.
- h. Gate must be terminated to source, $R \leq 100 \text{ k}\Omega$, whenever bias voltage is applied drain to source.

3.6 Electrical performance characteristics. Unless otherwise specified herein, the electrical performance characteristics are as specified in [1.3](#), [1.4](#), and [table I](#).

3.7 Electrical test requirements. The electrical test requirements shall be as specified in [table I](#).

3.8 Marking. Marking shall be in accordance with [MIL-PRF-19500](#).

3.9 Workmanship. Semiconductor devices shall be processed in such a manner as to be uniform in quality and shall be free from other defects that will affect life, serviceability, or appearance.

4. VERIFICATION

4.1 Classification of inspections. The inspection requirements specified herein are classified as follows:

- a. Qualification inspection (see [4.2](#)).
- b. Screening (see [4.3](#)).
- c. Conformance inspection (see [4.4](#) and [tables I and II](#)).

4.2 Qualification inspection. Qualification inspection shall be in accordance with [MIL-PRF-19500](#). Alternate flow is allowed for qualification inspection in accordance with [MIL-PRF-19500](#).

4.2.1 Group E qualification. Group E inspection shall be performed for qualification or re-qualification only. In case qualification was awarded to a prior revision of the specification sheet that did not request the performance of [table III](#) tests, the tests specified in [table III](#) herein that were not performed in the prior revision shall be performed on the first inspection lot of this revision to maintain qualification.

* 4.2.1.1 Single event effects (SEE). SEE (SEB/SEGR) shall be performed in accordance with TM1080 of [MIL-STD-750](#) at initial qualification and after process or design changes which may affect radiation hardness (see [table III](#) and [table IV](#)). Upon qualification, manufacturers shall provide the verification test conditions from section 5 of method 1080 of [MIL-STD-750](#) that were used to qualify the device for inclusion into section 6 of the slash sheet. End-point measurements shall be in accordance with [table II](#). SEE characterization data shall be made available upon request of the qualifying or acquiring activity.

* 4.2.3 Silicone die coating. When silicone die coating is used, method 5011 of MIL-STD-883 shall be performed on that coating in the full MIL-PRF-19500 qualification process.

4.3 Screening (JANS and JANTXV). Screening shall be in accordance with table E-IV of MIL-PRF-19500, and as specified herein. The following measurements shall be made in accordance with table I herein. Devices that exceed the limits of table I herein shall not be acceptable.

Screen (1) (2)	Measurements for JANS	Measurements for JANTXV
(3)	Gate stress test (see 4.3.1)	Gate stress test (see 4.3.1)
(3)	Method 3470 of MIL-STD-750, E _{AS} (see 4.3.2)	Method 3470 of MIL-STD-750, E _{AS} (see 4.3.2)
(3) 3c	Method 3161 of MIL-STD-750, thermal impedance, (see 4.3.3)	Method 3161 of MIL-STD-750, thermal impedance, (see 4.3.3)
5	Method 2052 of MIL-STD-750, PIND (see MIL-PRF-19500 and 4.3.4)	Not applicable
9	Subgroup 2 of table I herein	Not applicable
10	Method 1042 of MIL-STD-750, test condition B	Method 1042 of MIL-STD-750, test condition B
11	Subgroup 2 of table I herein. $\Delta I_{GSSF1} = \pm 20$ nA dc or ± 100 percent of initial value, whichever is greater. $\Delta I_{GSSR1} = \pm 20$ nA dc or ± 100 percent of initial value, whichever is greater. $\Delta I_{DSS1} = \pm 10$ μ A dc or ± 100 percent of initial value, whichever is greater.	Subgroup 2 of table I herein.
12	Method 1042 of MIL-STD-750, test condition A	Method 1042 of MIL-STD-750, test condition A
13	Subgroups 2 and 3 of table I herein $\Delta I_{GSSF1} = \pm 20$ nA dc or ± 100 percent of initial value, whichever is greater. $\Delta I_{GSSR1} = \pm 20$ nA dc or ± 100 percent of initial value, whichever is greater. $\Delta I_{DSS1} = \pm 10$ μ A dc or ± 100 percent of initial value, whichever is greater. $\Delta r_{DS(ON)1} = \pm 20$ percent of initial value. $\Delta V_{GS(TH)1} = \pm 20$ percent of initial value.	Subgroup 2 of table I herein $\Delta I_{GSSF1} = \pm 20$ nA dc or ± 100 percent of initial value, whichever is greater. $\Delta I_{GSSR1} = \pm 20$ nA dc or ± 100 percent of initial value, whichever is greater. $\Delta I_{DSS1} = \pm 10$ μ A dc or ± 100 percent of initial value, whichever is greater. $\Delta r_{DS(ON)1} = \pm 20$ percent of initial value. $\Delta V_{GS(TH)1} = \pm 20$ percent of initial value.

- (1) At the end of the test program, I_{GSSF1} , I_{GSSR1} , and I_{DSS1} are measured.
- (2) An out-of-family program to characterize I_{GSSF1} , I_{GSSR1} , I_{DSS1} , $V_{GS(th)1}$, and $r_{DS(ON)1}$ shall be invoked.
- (3) Shall be performed anytime after temperature cycling, screen 3a. JANTXV levels do not need to be repeated in screening requirements.

4.3.1 Gate stress test. Apply $V_{GS} = 24$ V minimum for $t = 250$ μ s minimum.

4.3.2 Single pulse avalanche energy (E_{AS}).

- a. Peak current $I_{AS} = I_{D1}$.
- b. Inductance: $\left[\frac{2E_{AS}}{(I_{D1})^2} \right] \left[\frac{V_{BR} - V_{DD}}{V_{BR}} \right]$ mH minimum.
- c. Gate to source resistor (R_{GS}) $25 \leq R_{GS} \leq 200 \Omega$.
- d. Supply voltage (V_{DD}) $V_{DD} = 25$ V dc, except $V_{DD} = 50$ V dc (2N7585U2), up to rated V_{DS} .
- e. Peak gate voltage (V_{GS}) 12 V, up to maximum rated V_{GS} .
- f. Initial case temperature $T_C = +25^\circ\text{C} +10^\circ\text{C}, -5^\circ\text{C}$.
- g. Number of pulses to be applied 1 pulse minimum.

4.3.3 Thermal impedance. The thermal impedance measurements shall be performed in accordance with method 3161 of [MIL-STD-750](#) using the guidelines in that method for determining I_M , I_H , t_H , t_{sw} , (and V_H where appropriate). See [table III](#), group E, subgroup 4 herein.

4.3.4 PIND. Not applicable in screening when devices are processed using alternative method and flow requirements approved by the qualifying activity, that includes incorporating the use of certified clean processing and silicone die coat. Instead, the PIND test performance shall be performed in group B3 and group C3, on a lot sample basis. PIND failures detected in group B or C will represent lot jeopardy and be evaluated for root cause and lot integrity.

4.4 Conformance inspection. Conformance inspection shall be in accordance with [MIL-PRF-19500](#). Alternate flow is allowed for conformance inspection in accordance with [MIL-PRF-19500](#).

4.4.1 Group A inspection. Group A inspection shall be conducted in accordance with table V of [MIL-PRF-19500](#) and [table I](#) herein.

4.4.2 Group B inspection. Group B inspection shall be conducted in accordance with the conditions specified for subgroup testing in table E-VIA (JANS) and table E-VIB (JANTXV) of [MIL-PRF-19500](#), and as follows.

4.4.2.1 Quality level JANS, table E-VIA of [MIL-PRF-19500](#).

Subgroup	Method	Condition
B3	1051	Test condition G, 100 cycles.
B3	2052	PIND, required if not performed in screening. (22 devices, $c = 0$ for large lots, 12 devices, $c = 0$ for small lots).
B4	1042	Intermittent operation life, condition D; $t_{on} = 30$ seconds minimum.
B5	1042	Accelerated steady-state gate bias, condition B, $V_{GS} = \text{rated}$; $T_A = +175^\circ\text{C}$, $t = 24$ hours minimum; or $T_A = +150^\circ\text{C}$, $t = 48$ hours minimum.
B5	1042	Accelerated steady-state reverse bias, condition A, $V_{DS} = \text{rated}$; $T_A = +175^\circ\text{C}$, $t = 120$ hours minimum; or $T_A = +150^\circ\text{C}$, $t = 240$ hours minimum.
B5	2037	Test condition D.

4.4.2.2 Quality level JANTXV, table E-VIB of MIL-PRF-19500.

<u>Subgroup</u>	<u>Method</u>	<u>Condition</u>
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B2	1051	Test condition G, 25 cycles.
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B3	1042	Intermittent operation life, condition D; $t_{on} = 30$ seconds minimum.
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4.4.3 Group C inspection. Group C inspection shall be conducted in accordance with the conditions specified for subgroup testing in table E-VII of MIL-PRF-19500 and as follows.

<u>Subgroup</u>	<u>Method</u>	<u>Condition</u>
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C2	2036	Not applicable.
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C3	2052	PIND, required if not performed in screening. (22 devices, $c = 0$ for large lots, 12 devices, $c = 0$ for small lots).
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C5	3161	See 4.3.3, $R_{\theta JC} = 0.50$ °C/W.
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C6	1042	Intermittent operation life, condition D; $t_{on} = 30$ seconds minimum.
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4.4.4 Group D inspection. Group D inspection shall be conducted in accordance with table E-VIII of MIL-PRF-19500 and table II herein.

4.4.5 Group E inspection. Group E inspection shall be conducted in accordance with the conditions specified for subgroup testing in table E-IX of MIL-PRF-19500 and as specified in table III herein.

4.5 Methods of inspection. Methods of inspection shall be as specified in the appropriate tables and as follows.

4.5.1 Pulse measurements. Conditions for pulse measurement shall be as specified in section 4 of MIL-STD-750.

TABLE I. Group A inspection.

Inspection <u>1/ 2/</u>	Method	MIL-STD-750	Symbol	Limits	Limits	Unit
		Condition		Min	Max	
<u>Subgroup 1</u>						
Visual and mechanical inspection	2071					
<u>Subgroup 2</u>						
Thermal impedance <u>3/</u>	3161	See 4.3.3	$Z_{\theta JC}$			°C/W
Breakdown voltage drain to source	3407	Bias condition C, $V_{GS} = 0$ V, $I_D = 1$ mA dc	$V_{(BR)DSS}$			
2N7579U2				100		V dc
2N7581U2				150		V dc
2N7583U2				200		V dc
2N7585U2				250		V dc
Gate to source voltage (threshold)	3403	$V_{DS} \geq V_{GS}$, $I_D = 1$ mA dc	$V_{GS(TH)1}$	2.0	4.0	V dc
Gate current	3411	$V_{GS} = +20$ V dc, bias condition C, $V_{DS} = 0$ V	I_{GSSF1}		+100	nA dc
Gate current	3411	$V_{GS} = -20$ V dc, bias condition C, $V_{DS} = 0$ V	I_{GSSR1}		-100	nA dc
Drain current	3413	$V_{GS} = 0$ V dc, bias condition C, $V_{DS} = 80$ percent of rated V_{DS}	I_{DSS1}		10	μA dc
Static drain to source on-state resistance	3421	$V_{GS} = 12$ V dc, condition A, pulsed (see 4.5.1), $I_D = I_{D2}$	$r_{DS(ON)1}$			
2N7579U2					0.010	Ω
2N7581U2					0.018	Ω
2N7583U2					0.028	Ω
2N7585U2					0.040	Ω
Forward voltage	4011	$V_{GS} = 0$ V dc, condition A, $I_D = I_{D1}$	V_{SD}		1.2	V dc

See footnotes at end of table.

TABLE I. Group A inspection - Continued.

Inspection 1/ 2/	MIL-STD-750		Symbol	Limits	Limits	Unit
	Method	Condition		Min	Max	
<u>Subgroup 3</u>						
High temperature operation		T _C = T _J = +125°C				
Gate current	3411	V _{GS} = ±20 V dc, bias condition C, V _{DS} = 0 V	I _{GSS2}		±200	nA dc
Drain current	3413	V _{GS} = 0 V dc, bias condition C, V _{DS} = 80 percent of rated V _{DS}	I _{DSS2}		25	µA dc
Static drain to source on-state resistance	3421	V _{GS} = 12 V dc, condition A, pulsed (see 4.5.1), I _D = I _{D2}	r _{DS(ON)3}			
2N7579U2					0.018	Ω
2N7581U2					0.036	Ω
2N7583U2					0.056	Ω
2N7585U2					0.088	Ω
Gate to source voltage (threshold)	3403	V _{DS} ≥ V _{GS} , I _D = 1 mA dc	V _{GS(TH)2}	1.0		V dc
Low temperature operation		T _C = T _J = -55°C				
Gate to source voltage (threshold)	3403	V _{DS} ≥ V _{GS(TH)3} , I _D = 1 mA dc	V _{GS(TH)3}		5.0	V dc
<u>Subgroup 4</u>						
Forward transconductance	3475	I _D = I _{D2} , V _{DD} = 15 V dc (see 4.5.1)	g _{FS}			
2N7579U2				60		S
2N7581U2				50		S
2N7583U2				40		S
2N7585U2				37		S
Switching time test	3472	I _D = rated I _{D1} ; V _{GS} = -12 V dc, R _G = 2.35 Ω (U2), V _{DD} = 50 percent of rated V _{DS}				
Turn-on delay time			t _{d(on)}		50	ns
Rise time			t _r		150	ns
Turn-off delay time			t _{d(off)}		100	ns
Fall time			t _f		50	ns

See footnotes at end of table.

TABLE I. Group A inspection - Continued.

Inspection <u>1/</u> <u>2/</u>	MIL-STD-750		Symbol	Limits	Limits	Unit
	Method	Condition		Min	Max	
<u>Subgroup 5</u> Safe operating area test (high voltage)	3474	$V_{DS} = 80$ percent of rated V_{DS} (see 1.3), $t_P = 10$ ms, I_D as specified on figure 5 .				
<u>Subgroup 6</u> Not applicable						
<u>Subgroup 7</u> Gate charge	3471	Condition B, $I_D = I_{D1}$, $V_{GS} = 12$ V dc $V_{DD} = 50$ percent of rated V_{DS}	$Q_{G(ON)}$ $Q_{G(OFF)}$			
On-state gate charge (turn-on and turn-off)						
2N7579U2					170	nC
2N7581U2					230	nC
2N7583U2					240	nC
2N7585U2					220	nC
Gate to source charge (turn-on and turn-off)			Q_{GS1} Q_{GS2}			
2N7579U2					60	nC
2N7581U2					70	nC
2N7583U2					70	nC
2N7585U2					50	nC
Gate to drain charge (turn-on and turn-off)			Q_{GD1} Q_{GD2}			
2N7579U2					80	nC
2N7581U2					90	nC
2N7583U2					60	nC
2N7585U2					70	nC
Reverse recovery time	3473	Condition A, $di/dt = -100$ A/ μ s, $V_{DD} \leq 50$ V, $I_D = I_{D1}$	t_{rr}			
2N7579U2						
2N7581U2					500	ns
2N7583U2					370	ns
2N7585U2					640	ns
					700	ns

1/ For sampling plan, see [MIL-PRF-19500](#).

2/ Electrical characteristics for the "U2A" suffix devices are identical to the "U2" suffix devices unless otherwise noted.

3/ For end-point measurements, this test is required for the following subgroups:
Group B, subgroups 2 and 3 (JANTXV).
Group B, subgroups 3 and 4 (JANS).
Group C, subgroup 2 and 6.
Group E, subgroup 1.

TABLE II. Group D inspection.

Inspection 1/ 2/ 3/ 4/	MIL-STD-750		Symbol	Pre-irradiation limits		Post-irradiation limits		Unit
	Method	Conditions		R, F and G		R, F and G		
				Min	Max	Min	Max	
<u>Subgroup 1</u>								
Not applicable								
<u>Subgroup 2</u>								
Steady-state total dose irradiation (V _{GS} bias) <u>5/</u>	1019	T _C = + 25°C Condition A, V _{GS} = 12 V;V _{DS} = 0						
Steady-state total dose irradiation (V _{DS} bias) <u>5/</u>	1019	Condition A, V _{GS} = 0; V _{DS} = 80 percent of rated V _{DS} (pre-irradiation)						
End-point electricals:								
Breakdown voltage, drain to source	3407	Bias condition C, V _{GS} = 0; I _D = 1 mA	V _(BR) DSS					
2N7579U2				100		100		V dc
2N7581U2				150		150		V dc
2N7583U2				200		200		V dc
2N7585U2				250		250		V dc
Gate to source voltage (threshold)	3403	V _{DS} ≥ V _{GS} I _D = 1 mA	V _{GS(th)} 1	2.0	4.0	2.0	4.0	V dc
Gate current	3411	Bias condition C, V _{GS} = +20 V; V _{DS} = 0	I _{GSSF} 1		100		100	nA dc
Gate current	3411	Bias condition C, V _{GS} = -20 V; V _{DS} = 0	I _{GSSR} 1		-100		-100	nA dc
Drain current	3413	Bias condition C, V _{GS} = 0, V _{DS} = 80 percent of rated V _{DS} (pre-irradiation)	I _{DSS}		10		10	μA dc
Static drain to source on-state voltage	3405	V _{GS} = 12 V; I _D = I _{D2} condition A, pulsed (see 4.5.1)	V _{DS(on)}					
2N7579U2					0.616		0.616	V dc
2N7581U2					0.931		0.931	V dc
2N7583U2					1.160		1.160	V dc
2N7585U2					1.291		1.291	V dc
Forward voltage source drain diode	4011	Bias condition A, V _{GS} = 0; I _D = I _{D1}	V _{SD}		1.2		1.2	V dc

- 1/ For sampling plan see [MIL-PRF-19500](#).
- 2/ Group D qualification may be performed prior to lot formation. Wafers qualified to these group D QCI requirements may be used for any other specification sheets utilizing the same die design.
- 3/ At the manufacturer's option, group D samples need not be subjected to the screening tests, and may be assembled in its qualified package or in any qualified package that the manufacturer has data to correlate the performance to the designated package.
- 4/ Electrical characteristics for the "U2A" suffix devices are identical to the "U2" suffix devices unless otherwise noted.
- 5/ Separate samples shall be pulled for each bias.

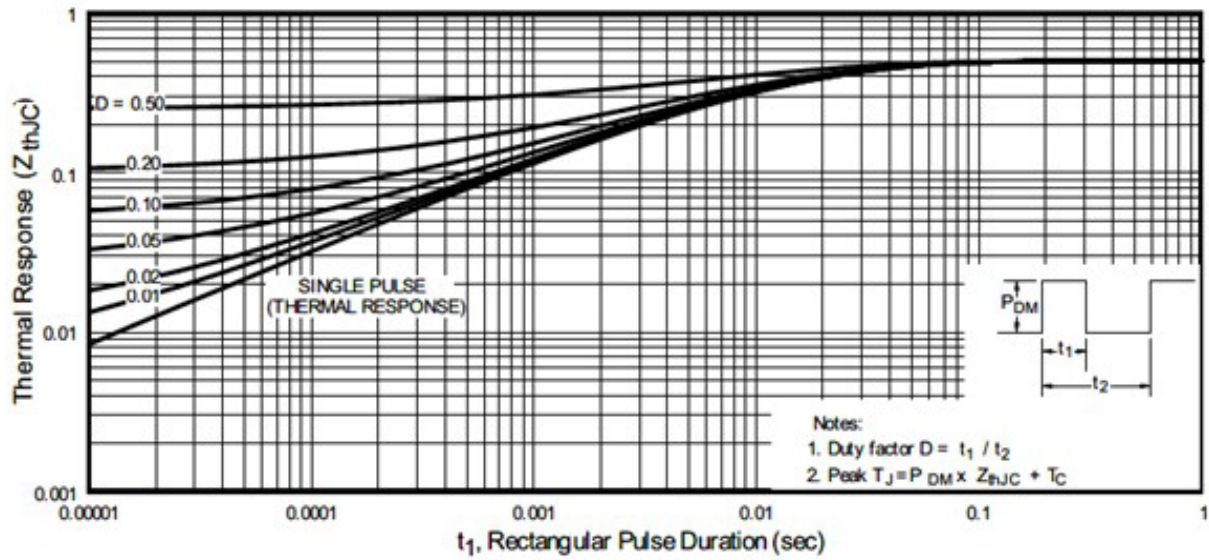
TABLE III. Group E inspection (all quality levels) for qualification or re-qualification only.

Inspection	MIL-STD-750		Sample plan
	Method	Conditions	
<u>Subgroup 1</u>			45 devices c = 0
Temperature cycling	1051	-55°C to +150°C, 500 cycles	
Hermetic seal	1071	As applicable.	
Fine leak			
Gross leak			
Electrical measurements		See table I , subgroup 2 herein.	
<u>Subgroup 2 1/</u>			45 devices c = 0
Steady-state gate bias	1042	Condition B, 1,000 hours.	
Electrical measurements		See table I , subgroup 2 herein.	
Steady-state reverse bias	1042	Condition A, 1,000 hours.	
Electrical measurements		See table I , subgroup 2 herein.	
<u>Subgroup 4</u>			Sample size N/A
Thermal impedance curves		See MIL-PRF-19500 .	
<u>Subgroup 5</u>			3 devices c = 0
Barometric pressure 2N7585U2 only	1001	To 70,000 feet	
<u>Subgroup 10</u>			22 devices c = 0
Commutating diode for safe operating area test procedure for measuring dv/dt during reverse recovery of power MOSFET transistors or insulated gate bipolar transistors	3476	Test conditions shall be derived by the manufacturer	
<u>Subgroup 11</u>			
SEE 2/ 3/	1080	See MIL-STD-750 method 1080 and 6.2 .	

[1/](#) A separate sample for each test shall be pulled.

[2/](#) Group E qualification of SEE testing may be performed prior to lot formation. Qualification may be extended to other specification sheets utilizing the same structurally identical die design.

[3/](#) Device qualification to a higher level linear energy transfer (LET) is sufficient to qualify all lower level LETs.



* FIGURE 3. Thermal impedance curve.

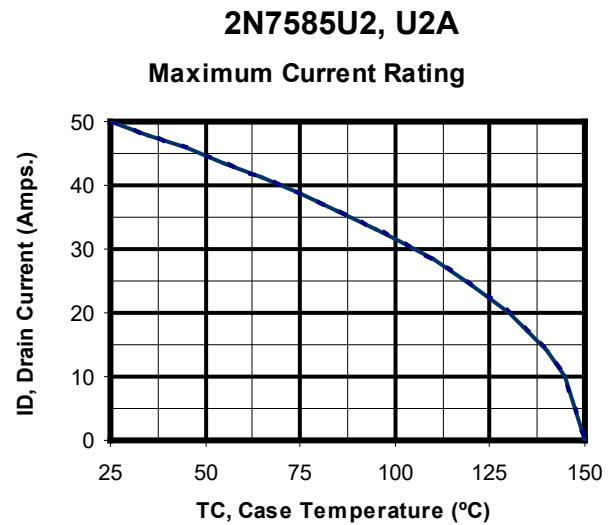
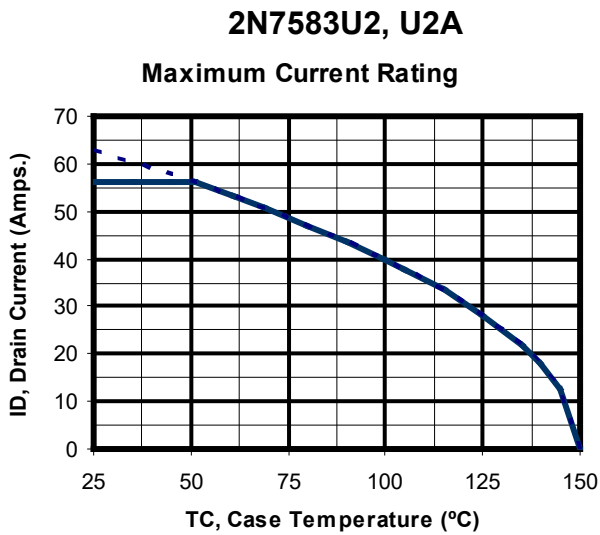
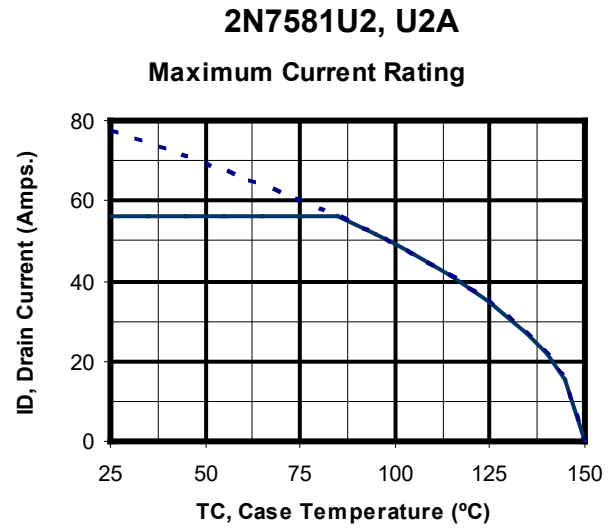
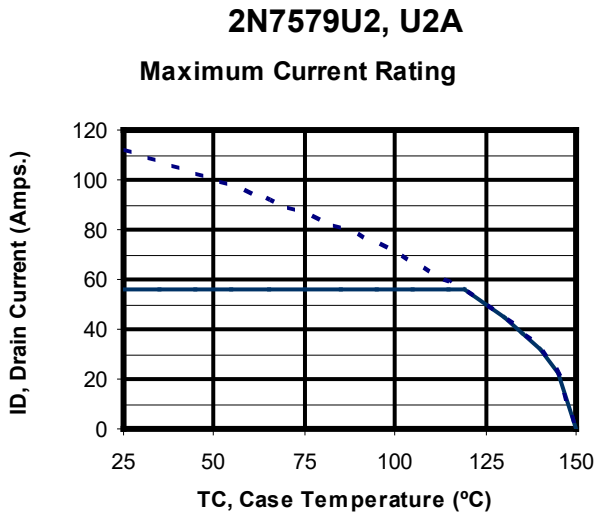


FIGURE 4. Maximum drain current versus case temperature graphs.

2N7579U2, U2A

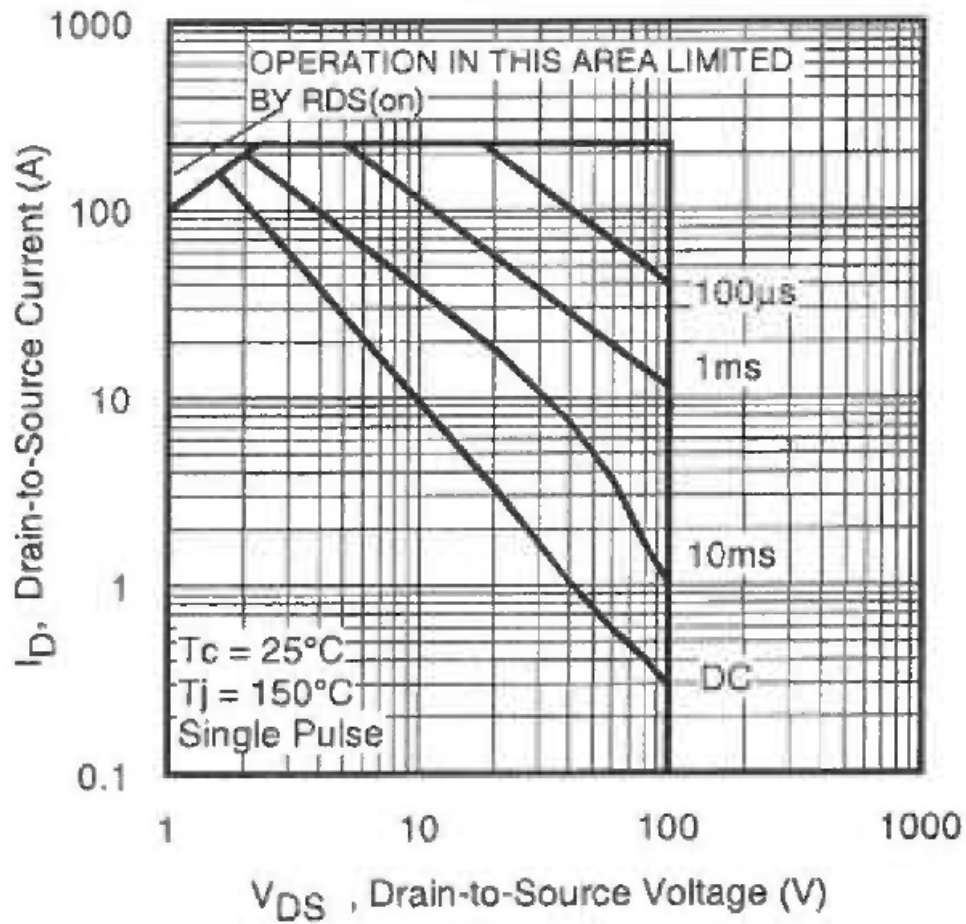


FIGURE 5. Safe operating area graph.

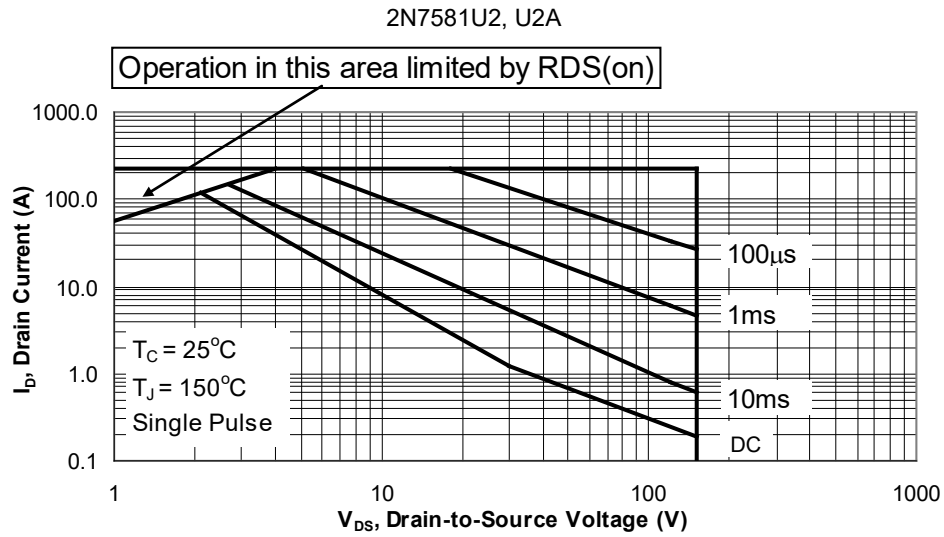
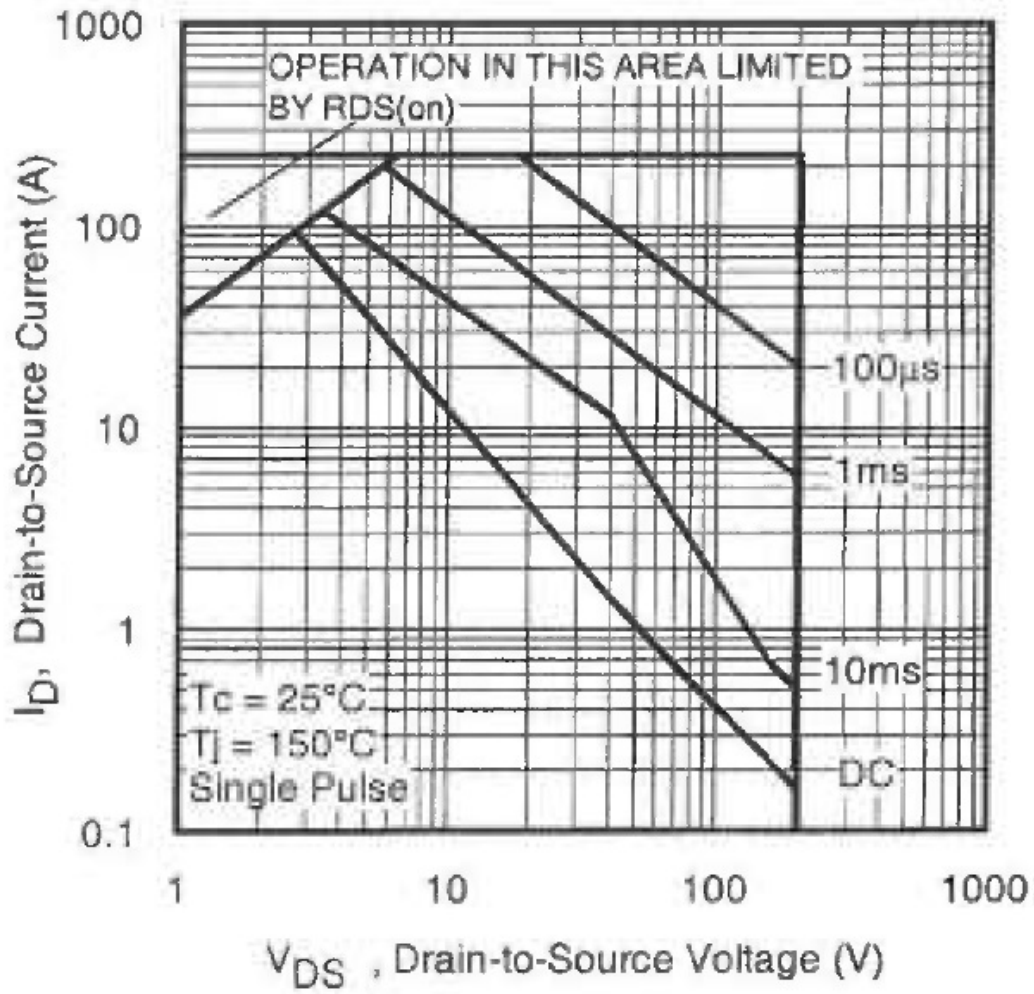


FIGURE 5. Safe operating area graph - Continued.



2N7583U2, U2A

FIGURE 5. Safe operating area graph - Continued.

2N7585U2, U2A

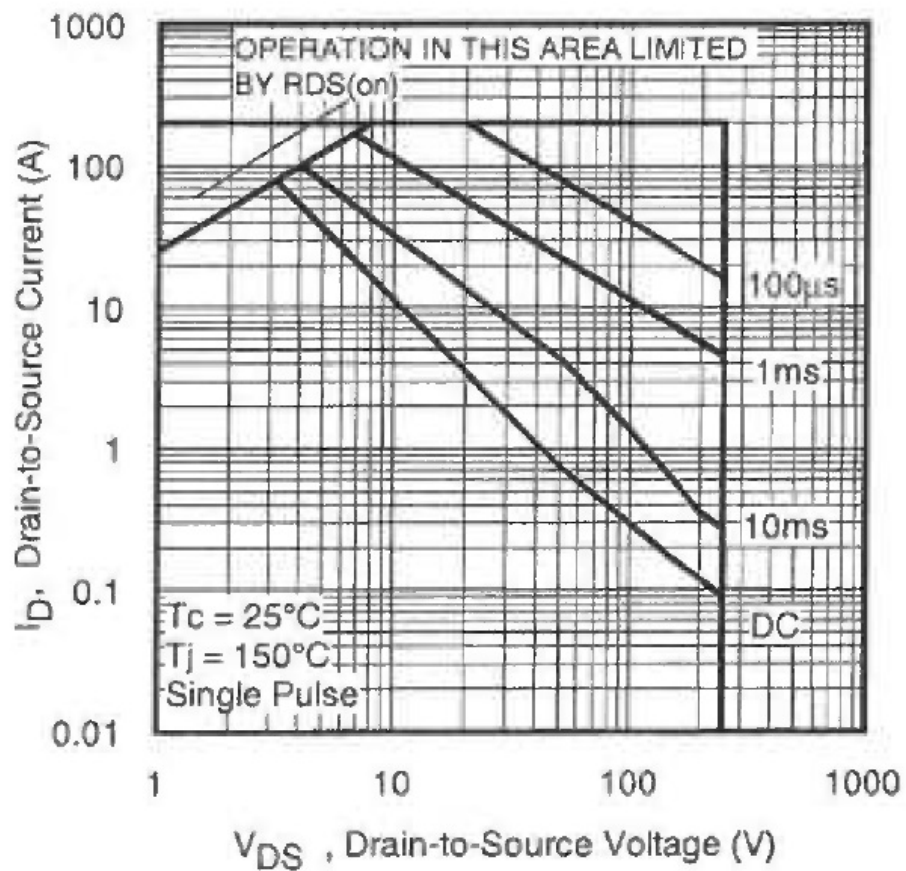


FIGURE 5. Safe operating area graph - Continued.

5. PACKAGING

5.1 Packaging. For acquisition purposes, the packaging requirements shall be as specified in the contract or order (see 6.2). When packaging of materiel is to be performed by DoD or in-house contractor personnel, these personnel need to contact the responsible packaging activity to ascertain packaging requirements. Packaging requirements are maintained by the Inventory Control Point's packaging activities within the Military Service or Defense Agency, or within the Military Service's system commands. Packaging data retrieval is available from the managing Military Department's or Defense Agency's automated packaging files, CD-ROM products, or by contacting the responsible packaging activity.

6. NOTES

(This section contains information of a general or explanatory nature that may be helpful, but is not mandatory. The notes specified in MIL-PRF-19500 are applicable to this specification.)

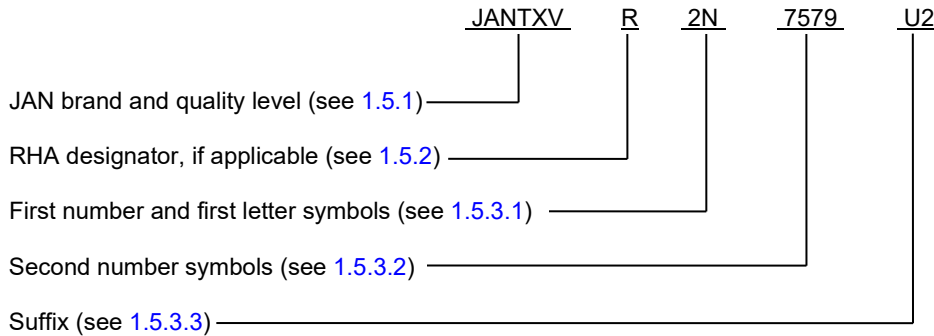
6.1 Intended use. Semiconductors conforming to this specification are intended for original equipment design applications and logistic support of existing equipment.

6.2 Acquisition requirements. Acquisition documents should specify the following:

- a. Title, number, and date of this specification.
- b. Packaging requirements (see 5.1).
- c. Lead finish (see 3.4.1).
- d. The complete PIN, see 1.5 and 6.5.
- e. For acquisition of RHA designated devices, table II, subgroup 1 testing of group D herein is optional. If subgroup 1 is desired, it should be specified in the contract or order.
- f. If SEE testing data is desired, it should be specified in the contract or order.
- g. If specific SEE characterization conditions are desired (see section 6.7 and table IV), manufacturer's cage code should be specified in the contract or order.

* 6.3 Qualification. With respect to products requiring qualification, awards will be made only for products which are, at the time of award of contract, qualified for inclusion in Qualified Manufacturers List (QML 19500) whether or not such products have actually been so listed by that date. The attention of the contractors is called to these requirements, and manufacturers are urged to arrange to have the products that they propose to offer to the Federal Government tested for qualification in order that they may be eligible to be awarded contracts or orders for the products covered by this specification. Information pertaining to qualification of products may be obtained from DLA Land and Maritime Weapons Support, ATTN: VQE, P.O. Box 3990, Columbus, OH 43218-3990 or e-mail vqe.chief@dla.mil. An online listing of products qualified to this specification may be found in the Qualified Products Database (QPD) at <https://qpldocs.dla.mil>.

6.4 PIN construction example. The PINs for encapsulated devices are construction using the following form.



6.5 List of PINs. The following is a list of possible PINs available on this specification sheet.

PINs for devices of the "TXV" quality level	PINs for devices of the "TXV" quality level with RHA (1)	PINs for devices of the "S" quality level	PINs for devices of the "S" quality level with RHA (1)
JANTXV2N7579U2	JANTXV#2N7579U2	JANS2N7579U2	JANS#2N7579U2
JANTXV2N7581U2	JANTXV#2N7581U2	JANS2N7581U2	JANS#2N7581U2
JANTXV2N7583U2	JANTXV#2N7583U2	JANS2N7583U2	JANS#2N7583U2
JANTXV2N7585U2	JANTXV#2N7585U2	JANS2N7585U2	JANS#2N7585U2
JANTXV2N7579U2A	JANTXV#2N7579U2A	JANS2N7579U2A	JANS#2N7579U2A
JANTXV2N7581U2A	JANTXV#2N7581U2A	JANS2N7581U2A	JANS#2N7581U2A
JANTXV2N7583U2A	JANTXV#2N7583U2A	JANS2N7583U2A	JANS#2N7583U2A
JANTXV2N7585U2A	JANTXV#2N7585U2A	JANS2N7585U2A	JANS#2N7585U2A

(1) The number sign (#) represent one of three RHA designators available on this specification sheet ("R", "F", or "G"). The PIN is also available without a RHA designator.

6.6 Substitution information. Devices covered by this specification are substitutable for the manufacturer's and user's Part or Identifying Number (PIN) (without JAN and RHA prefix). This information in no way implies that manufacturer's PINs are substitutable for the military PIN.

Preferred types military PIN	Commercial PIN	Preferred types military PIN	Commercial PIN
2N7579U2	IRHNA67160	2N7579U2A	IRHNS67160
2N7581U2	IRHNA67164	2N7581U2A	IRHNS67164
2N7583U2	IRHNA67260	2N7583U2A	IRHNS67260
2N7585U2	IRHNA67264	2N7585U2A	IRHNS67264

6.7 Application data.

6.7.1 Manufacturer specific irradiation data. Each manufacturer qualified to this specification sheet has characterized its devices to the requirements of MIL-STD-750 method 1080 and as specified herein. Since each manufacturer's characterization conditions can be different and can vary by the version of method 1080 qualified to, the MIL-STD-750 method 1080 revision version date and conditions used by each manufacturer for characterization have been listed here (see table IV) for information only. SEE conditions and figures listed in section 6 are current as of the date of this specification sheet, please contact the manufacturer for the most recent conditions.

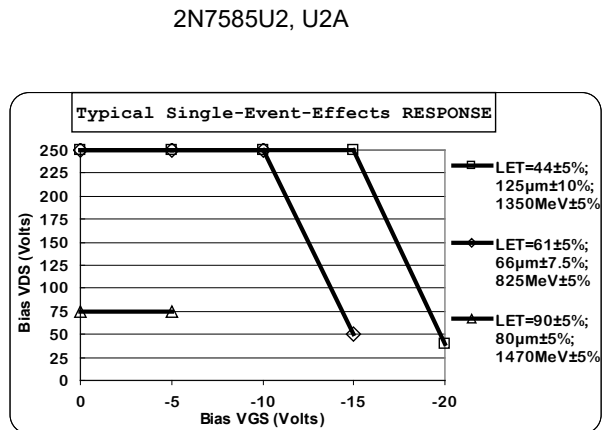
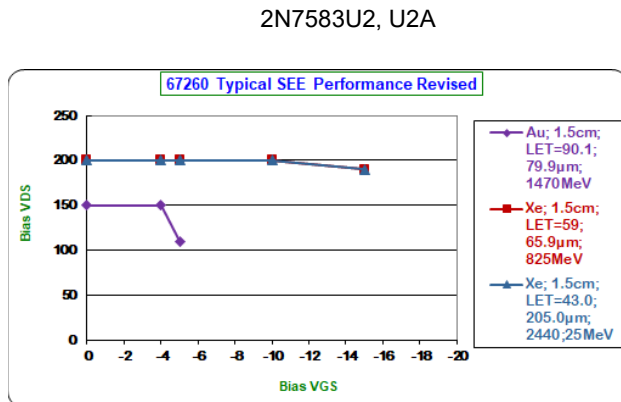
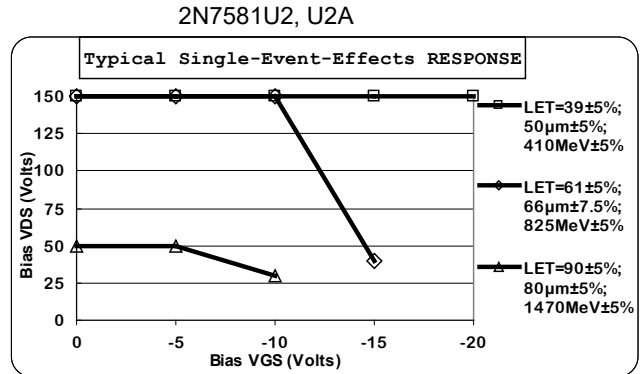
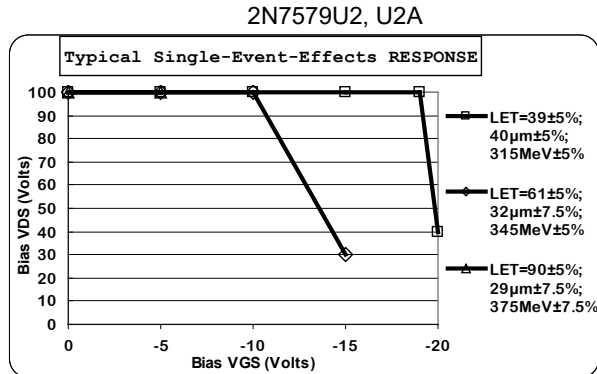
TABLE IV. Manufacturers characterization conditions.

Manufactures cage	Inspection	MIL-STD-750		Sample plan
		Method	Conditions	
69210 (Applicable to devices with a date code of March 2011 and older)	SEE 1/	1080	See MIL-STD-750E method 1080.0 dated 20 November 2006. See figure 6.	3 devices
	Electrical measurements		I_{GSSF1} , I_{GSSR1} , and I_{DSS1} in accordance with table I, subgroup 2	
	SEE irradiation:		Fluence = $3E5 \pm 20$ percent ions/cm ² Flux = $2E3$ to $2E4$ ions/cm ² /sec, temperature = $25^\circ \pm 5^\circ C$	
	2N7579U2, U2A		Surface LET = 39 MeV-cm ² /mg $\pm 5\%$, range = 40 $\mu m \pm 5\%$, energy = 315 MeV $\pm 5\%$ In-situ bias conditions: $V_{DS} = 100 V$ and $V_{GS} = -19 V$; $V_{DS} = 40 V$ and $V_{GS} = -20 V$ (typical 3.80 MeV/nucleon at Texas A & M Cyclotron)	
	2N7581U2, U2A		Surface LET = 39 MeV- cm ² /mg $\pm 5\%$, range = 50 $\mu m \pm 5\%$, energy = 410 MeV $\pm 5\%$ In-situ bias conditions: $V_{DS} = 150 V$ and $V_{GS} = -20 V$ (typical 4.90 MeV/nucleon at Texas A & M Cyclotron)	
	2N7583U2, U2A		Surface LET = 43 MeV- cm ² /mg $\pm 5\%$, range = 205 $\mu m \pm 5\%$, energy = 2440 MeV $\pm 5\%$ In-situ bias conditions: $V_{DS} = 200 V$ and $V_{GS} = -10 V$; $V_{DS} = 190 V$ and $V_{GS} = -15 V$ (typical 18.93 MeV/nucleon at Texas A & M Cyclotron)	
	2N7585U2, U2A		Surface LET = 44 MeV- cm ² /mg $\pm 5\%$, range = 125 $\mu m \pm 10\%$, energy = 1350 MeV $\pm 5\%$ In-situ bias conditions: $V_{DS} = 250 V$ and $V_{GS} = -15 V$; $V_{DS} = 40 V$ and $V_{GS} = -20 V$ (typical 10.05 MeV/nucleon at Texas A & M Cyclotron)	
	2N7579U2, U2A		Surface LET = 61 MeV- cm ² /mg $\pm 5\%$, range = 32 $\mu m \pm 7.5\%$, energy = 345 MeV $\pm 5\%$ In-situ bias conditions: $V_{DS} = 100 V$ and $V_{GS} = -10 V$; $V_{DS} = 30 V$ and $V_{GS} = -15 V$ (typical 2.70 MeV/nucleon at Texas A & M Cyclotron)	
	2N7581U2, U2A		Surface LET = 61 MeV- cm ² /mg $\pm 5\%$, range = 66 $\mu m \pm 7.5\%$, energy = 825 MeV $\pm 5\%$ In-situ bias conditions: $V_{DS} = 150 V$ and $V_{GS} = -10 V$; $V_{DS} = 40 V$ and $V_{GS} = -15 V$ (typical 6.40 MeV/nucleon at Texas A & M Cyclotron)	

TABLE IV. Manufacturers characterization conditions- Continued

Manufactures cage	Inspection	MIL-STD-750		Sample plan
		Method	Conditions	
*	2N7583U2, U2A		Surface LET = 59 MeV- cm ² /mg ±5%, range = 65.9 μm ±7.5%, energy = 825 MeV ±5% In-situ bias conditions: V _{DS} = 200 V and V _{GS} = -10 V; V _{DS} = 190 V and V _{GS} = -15 V (typical 6.41 MeV/nucleon at Texas A & M Cyclotron)	
	2N7585U2, U2A		Surface LET = 61 MeV- cm ² /mg ±5%, range = 66 μm ±7.5%, energy = 825 MeV ±5% In-situ bias conditions: V _{DS} = 250 V and V _{GS} = -10 V; V _{DS} = 50 V and V _{GS} = -15 V (typical 6.41 MeV/nucleon at Texas A & M Cyclotron)	
	2N7579U2, U2A		Surface LET = 90 MeV- cm ² /mg ±5%, range = 29 μm ±7.5%, energy = 375 MeV ±7.5% In-situ bias conditions: V _{DS} = 100 V and V _{GS} = -5 V (typical 1.88 MeV/nucleon at Texas A & M Cyclotron)	
	2N7581U2, U2A		Surface LET = 90 MeV- cm ² /mg ±5%, range = 80 μm ±5%, energy = 1470 MeV ±5% In-situ bias conditions: V _{DS} = 50 V and V _{GS} = -5 V; V _{DS} = 30 V and V _{GS} = -10 V (typical 7.47 MeV/nucleon at Texas A & M Cyclotron)	
*	2N7583U2, U2A		Surface LET = 90.1 MeV- cm ² /mg ±5%, range = 79.9 μm ±5%, energy = 1470 MeV ±5% In-situ bias conditions: V _{DS} = 150 V and V _{GS} = -4 V V _{DS} = 110 V and V _{GS} = -5 V (typical 11.40 MeV/nucleon at Texas A & M Cyclotron)	
	2N7585U2, U2A		Surface LET = 90 MeV- cm ² /mg ±5%, range = 80 μm ±5%, energy = 1470 MeV ±5% In-situ bias conditions: V _{DS} = 75 V and V _{GS} = -5 V (typical 7.47 MeV/nucleon at Texas A & M Cyclotron)	
	Electrical measurements		I _{GSSF1} , I _{GSSR1} , and I _{DSS1} in accordance with table I , subgroup 2	
Upon qualification, all manufacturers should provide the verification test conditions to be added to this table.				

1/ I_{GSSF1}, I_{GSSR1}, and I_{DSS1} was examined before and following SEE irradiation to determine acceptability for each bias condition. Other test conditions in accordance with [table I](#), subgroup 2, may be performed at the manufacturer's option.



* FIGURE 6. SEE safe operating area graph.

* 6.8 Request for new types and configurations. Requests for new device types or configurations for inclusions in this specification sheet should be submitted to: DLA Land and Maritime Weapons Support, ATTN: VAC, Post Office Box 3990, Columbus, OH 43218-3990 or by electronic mail at Semiconductor@dla.mil.

~~— 6.9 Amendment notations. The margins of this specification are marked with asterisks to indicate modifications generated by this amendment. This was done as a convenience only and the Government assumes no liability whatsoever for any inaccuracies in these notations. Bidders and contractors are cautioned to evaluate the requirements of this document based on the entire content irrespective of the marginal notations.~~

* 6.9 Changes from previous issue. The margins of this specification are marked with an asterisk to indicate where changes from the previous issue were made. This was done as a convenience only and the Government assumes no liability whatsoever for any inaccuracies in these notations. Bidders and contractors are cautioned to evaluate the requirements of this document based on the entire content irrespective of the marginal notations and relationship to the previous issue.

CONCLUDING MATERIAL

Custodians:
Army - CR
* Navy - SH
Air Force - 85
NASA - NA
DLA - CC

Review activity:
Air Force - 19

Preparing activity:
DLA - CC

(Project 5961-2026-072)

NOTE: The activities listed above were interested in this document as of the date of this document. Since organizations and responsibilities can change, you should verify the currency of the information above using the ASSIST Online database at <https://assist.dla.mil>.